HE8801

GaAlAs IRED

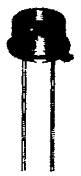
HITACHI/(OPTOELECTRONICS) T-41-13

Description

HE8801 is a 0.8 μm GaAlAs infrared emitting diode with single heterojunction structure.

Wide radiant directionality makes it suitable as a light source in various types of optical equipment.

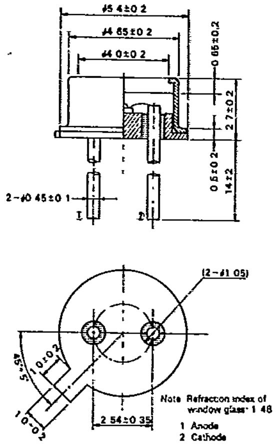
Hermetic sealing of the package achieves high reliability.



Features

- High efficiency and high power output
- Narrow spectral width
- Wide radiant directionality

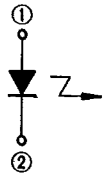
Package Dimensions



(Unit: mm)

SG-type

Internal Circuit



Absolute Maximum Ratings ($T_C = 25°C$)

Items	Symbols	Values	Units
Forward current	I_F	200	mA
Reverse voltage	V_R	3	V
Tolerable power dissipation	P_d	400	mW
Operating temperature	T_{opr}	−20 to +60	°C
Storage temperature	T_{stg}	−40 to +90	°C

Optical and Electrical Characteristics ($T_C = 25°C$)

Items	Symbols	min.	typ.	max.	Units	Test conditions
Optical output power	P_O	6	20		mW	I_F = 150 mA
Peak wavelength	λ_p	800	880	900	nm	I_F = 150 mA
Spectral width	$\Delta\lambda$		30	60	nm	I_F = 150 mA
Forward voltage	V_F		1.7	2.3	V	I_F = 150 mA
Reverse current	I_R			100	μA	V_R = 3 V
Capacitance	C_t		10		pF	V_R = 0 V, f = 1 MHz
Rise time	t_r		12		ns	I_F = 50 mA
Fall time	t_f		12		ns	I_F = 50 mA